PC851XNNSZ1H Series

DIP 4pin High Collector-emitter Voltage Photocoupler



Description

PC851XNNSZ1H Series contains an IRED optically coupled to a phototransistor.

It is packaged in a 4-pin DIP, available in SMT gullwing lead-form option.

Input-output isolation voltage(rms) is 5.0kV. Collector-emitter voltage is 350V.

■ Features

- 1. 4pin DIP package
- 2. Double transfer mold package (Ideal for Flow Soldering)
- 3. High collector-emitter voltage (V_{CEO}: 350V)
- 4. High isolation voltage between input and output (V_{iso(rms)}: 5.0 kV)
- 5. Lead-free and RoHS directive compliant

■ Agency approvals/Compliance

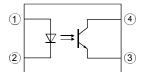
- Recognized by UL1577, file No. E64380 (as model No. PC851)
- 2. Package resin: UL flammability grade (94V-0)

■ Applications

- 1. Telephone line interface/isolation
- 2. Interface to power supply circuit
- 3. Controller for SSRs, DC moters

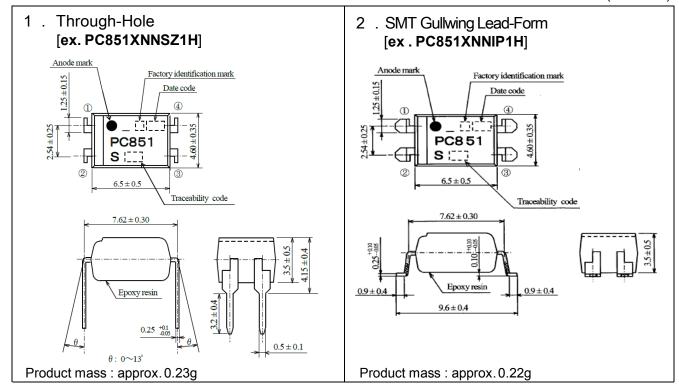


■ Internal Connection Diagram



- 1 Anode
- ② Cathode
- 3 Emitter
- 4 Collector

■ Outline (Unit:mm)





Date code indication (Ex.)

3-digit number shall be marked the age indication of 1-digit number, and week code of 2-digit number. Week code "01" indicate the week including the first Thursday of January. And later, Monday is the starting point.

Year Wee	ek
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Date code	MON	TUE	WED	THU	FRI	SAT	SUN
652	12/26	12/27	12/28	12/29	12/30	12/31	1/1
701	1/2	1/3	1/4	1/5	1/6	1/7	1/8
702	1/9	1/10	1/11	1/12	1/13	1/14	1/15
703	1/16	1/17	1/18	1/19	1/20	1/21	1/22
	•		•		•	•	•
	-						
		•		•	•	•	•
752	12/11	12/12	12/13	12/14	12/15	12/16	12/17
751	12/18	12/19	12/20	12/21	12/22	12/23	12/24
752	12/25	12/26	12/27	12/28	12/29	12/30	12/31
801	1/1	1/2	1/3	1/4	1/5	1/6	1/7

Factory identification mark and Plating material

Factory identification Mark	Country of origin	Plating material
K	Japan	SnBi (Bi : 1∼4%)

Rank mark

Refer to the Model Line-up table.



■ Absolute Maximum Ratings

(T_a=25°C)

	Parameter	Symbol	Rating	Unit
	Forward current	I_F	50	mA
ut	*1 Peak forward current	I_{FM}	1	A
Input	Reverse voltage	V_R	6	V
	Power dissipation	P	70	mW
	Collector-emittervoltage	V_{CEO}	350	V
Output	Emitter-collector voltage	V_{ECO}	6	V
Out	Collector current	I_{C}	50	mA
	Collector power dissipation	Pc	150	mW
	Total power dissipation	P _{tot}	200	mW
*2 Isolation voltage		V _{iso (rms)}	5	kV
Operating temperature		Topr	-25 to +100	°C
Storage temperature		T _{stg}	-55 to +125	°C
*3 5	Soldering temperature	T _{sol}	270	°C

^{*1} Pulse width≤100µs, Duty ratio: 0.001 *2 40 to 60%RH, AC for 1 minute *3 For 10s

■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

	•						(- a	50)
	Para	meter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward voltage		V_{F}	I _F =20mA	_	1.2	1.4	V	
Input	Reverse Cu	rrent	I_R	V _R =4V	_	_	10	μΑ
	Terminal ca	pacitance	Ct	V=0, f=1kHz	_	30	250	pF
	Dark currer	nt	I_{CEO}	V _{CE} =200V, I _F =0	_	_	1	μΑ
Output	Collector-en	nitter breakdown voltage	BV _{CEO}	I _C =0.1mA, I _F =0	350	_	_	V
E	Emitter-collector breakdown voltage		BV_{ECO}	I _E =10μA, I _F =0	6	_	_	V
Collector current	irrent	Ic	I _F =5mA, V _{CE} =5V	2.0	4.0	-	mA	
	Collector-emitter saturation voltage		V _{CE (sat)}	I _F =20mA, I _C =1mA	_	0.1	0.3	V
Transfer	Isolation res	sistance	R _{ISO}	DC500V, 40 to 60%RH	5×10 ¹⁰	1×10 ¹¹	-	Ω
charac-	Floating cap	pacitance	C_{f}	V=0, f=1MHz	_	0.6	1.0	pF
Respon time	Cut-off frequency		fc	V _{CE} =5V, I _C =2mA, R _L =100Ω, -3dB	_	50	-	kHz
	Risetime	$t_{\rm r}$	Var=2V Ia=2mA Pr=1000	_	4	10	μs	
	1. *	Falltime	t_{f}	$V_{CE}=2V$, $I_{C}=2mA$, $R_{L}=100\Omega$	_	5	12	μs



■ Model Line-up

Lead Form	Through-Hole	SMT Gullwing
Package	Sleeve	Taping
	100pcs/sleeve	2,000pcs/reel
Model No.	PC851XNNSZ1H	PC851XNNIP1H

Please contact a local SHARP sales representative to inquire about production status.



Fig.1 Forward Current vs. Ambient Temperature

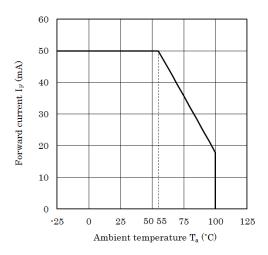


Fig.3 Collector Power Dissipation vs.
Ambient Temperature

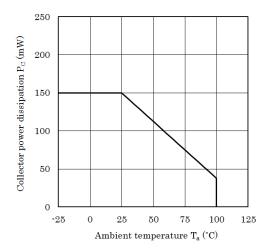


Fig.5 Peak Forward Current vs. Duty Ratio

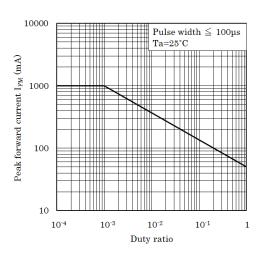


Fig.2 Diode Power Dissipation vs.
Ambient Temperature

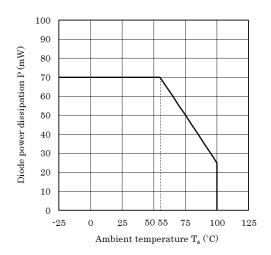


Fig.4 Total Power Dissipation vs. Ambient Temperature

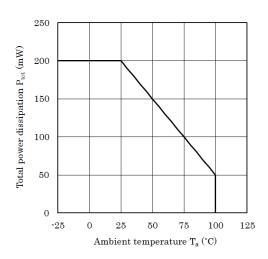


Fig.6 Forward Current vs. Forward Voltage

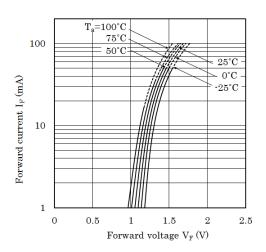




Fig.7 Current Transfer Ratio vs. Forward Current

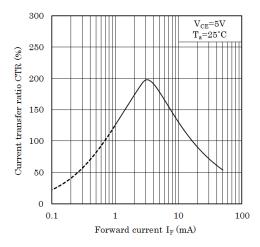


Fig.9 Relative Current Transfer Ratio vs.
Ambient Temperature

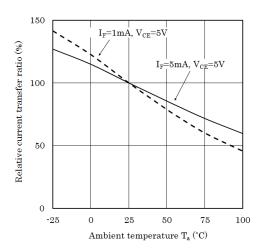


Fig.11 Collector Dark Current vs. Ambient Temperature

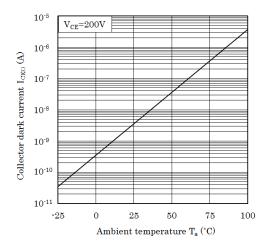


Fig.8 Collector Current vs. Collector-emitter Voltage

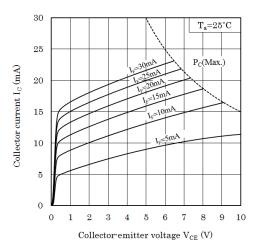


Fig.10 Collector - emitter Saturation Voltage vs. Ambient Temperature

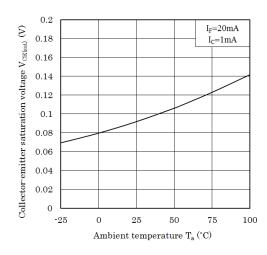


Fig.12 Collector-emitter Saturation Voltage vs. Forward Current

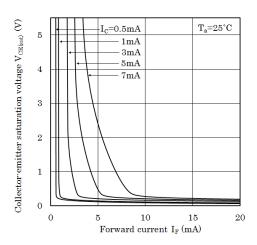
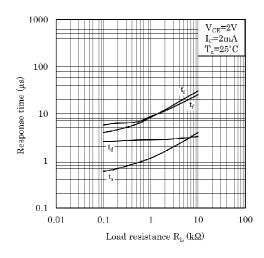




Fig.13 Response Time vs. Load Resistance

Fig.14 Test Circuit for Response Time



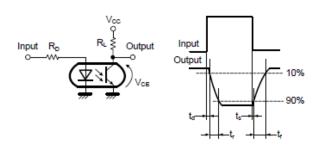
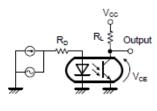


Fig.15 Frequency Response

 $\begin{array}{c} 5 \\ 0 \\ 0 \\ -5 \\ -10 \\ -15 \\ -20 \\ 0.1 \\ \end{array} \begin{array}{c} V_{CE} = 5V \\ I_C = 2mA \\ T_s = 25 ^{\circ}C \\ \end{array}$

Fig.16 Test Circuit for Frequency Response



Remarks: Please be aware that all data in the graph are just for reference and not for guarantee.



■ Design Considerations

• Design guide

While operating at I_F<1mA, CTR variation may increase.

Please make design considering this fact.

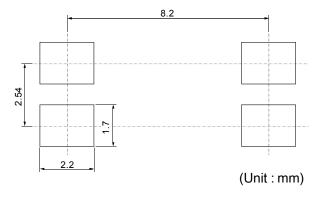
This product is not designed against irradiation and incorporates non-coherent IRED.

Degradation

In general, the emission of the IRED used in photocouplers will degrade over time. In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

• Recommended foot print (reference)

SMT Gullwing lead-form



[☆] For additional design assistance, please review our corresponding Optoelectronic Application Notes.



■ Manufacturing Guidelines

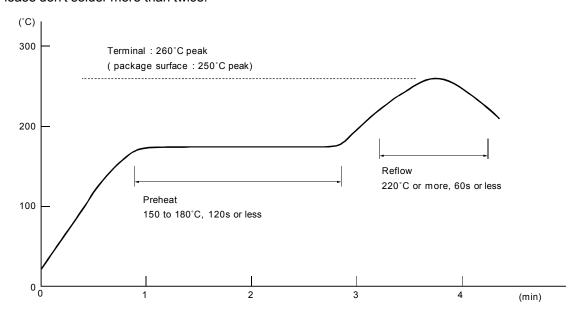
Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below.

Soldering should not exceed the curve of temperature profile and time.

Please don't solder more than twice.



Flow Soldering:

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 270°C and within 10s.

Preheating is within the bounds of 100 to 150°C and 30 to 80s.

Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C.

Please don't solder more than twice.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBB and PBDE are not used in this product at all.

- The RoHS directive(2011/65/EU)
 This product complies with the RoHS directive(2011/65/EU)
 Object substances: mercury, lead, cadmium, hexavalent chromium, polybrominated biphenyls
 (PBB) and polybrominated diphenyl ethers (PBDE)
- (2) Content of six substances specified in Management Methods for Control of Pollution Caused by Electronic Information Products Regulation (Chinese: 电子信息产品污染控制管理办法).

		Hazardous Substances					
Category	Lead (Pb)	Mercury (Hg)	Cadmium (Cd)	Hexavalent chromium (Cr ⁶⁺)	Polybrominated biphenyls (PBB)	Polybrominated diphenyl ethers (PBDE)	
Photocoupler	0	0	0	0	0	0	

This table is prepared in accordance with the provisions of SJ/T 11364.

 : Indicates that said hazardous substance contained in all of the homogeneous materials for this part is below the limit requirement of GB/T 26572.



■ Package specification

Sleeve package

Through-Hole

Package materials

Sleeve: HIPS/PS or PC (with anti-static material)

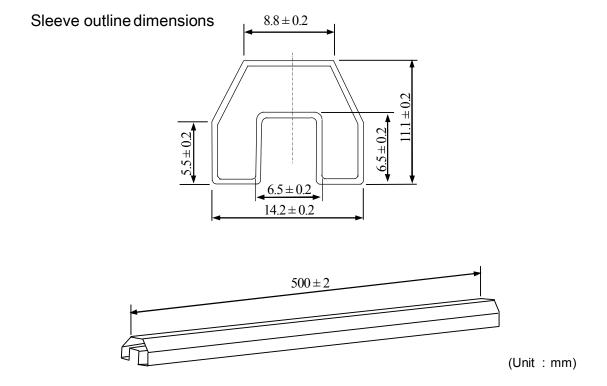
Stopper: EPM

Package method

MAX. 100pcs. of products shall be packaged in a sleeve and both of sleeve edges shall be fixed by stoppers.

MAX. 25 sleeves (Product: 2,500pcs.) above shall be packaged in inner case and sealed by tape.

Max 2 bags(product: 5,000pcs) above shall be packaged in packing case, and put a cushioning material inside.





Tape and Reel package

SMT Gullwing

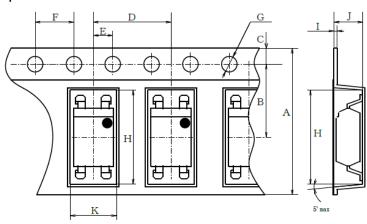
Package materials

Carrier tape: PS

Cover tape: PET (three layer system)

Reel: PS

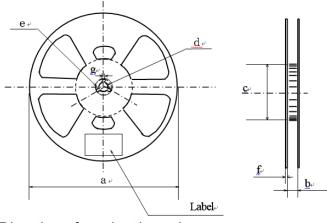
Carrier tape structure and Dimensions



Dimensions List (Unit: mm)

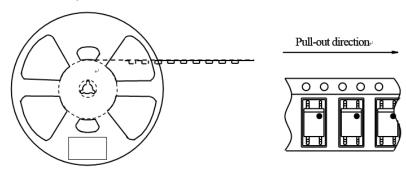
A	В	С	D	Е	F	G
$16.0^{\pm0.3}$	7.5 ^{±0.1}	1.75 ^{±0.10}	8.0 ^{±0.1}	2.0 ^{±0.1}	4.0 ^{±0.1}	\$\dphi 1.5^{+0.1}_{-0.0}\$
Н	I	J	K			
10.3 ^{±0.1}	0.40 ^{±0.05}	4.0 ^{±0.1}	5.3 ^{±0.1}			

Reel structure and Dimensions



Dimensio	ns List	(U	nit: mm)
a	b	c	d
ф330	17.5 ^{±1.5}	φ100±1	ф13.0 ^{±0.5}
e	f	g	
φ21.0 ^{±1}	2.0±0.5	2.0±0.5	

Direction of product insertion



[Packing: 2,000pcs/reel]